

AMENDMENTS TO THE CLAIMS

1. (Currently amended) A semiconductor device comprising:

a semiconductor chip,

a protective insulating layer comprising a coating layer covering the surface of the semiconductor chip;

a plurality of connecting conductors connected to the surface of the semiconductor chip and penetrating the coating layer beyond the outside surface of the coating layer, wherein the connecting conductors are connected to bumps as external terminals beyond the outside surface of the coating layer, and wherein the connecting conductors do not include wiring layers and the bumps;

wherein the connecting conductor includes a plurality of layers formed of same material and at least one of the layers is formed as a stress-absorbing layer having lower hardness than other layer.
2. (Original) The semiconductor device according to claim 1, wherein said connecting conductor is formed from anisotropic conductive material.
3. (Original) The semiconductor device according to claim 1, wherein said connecting conductor is formed from conductive material containing metal particles.
4. (Original) The semiconductor device according to claim 1, wherein said connecting conductor is formed by means of stacking a plurality of layers in a staggered manner.

5. (Original) The semiconductor device according to claim 4, wherein said plurality of layers of the connecting conductor are formed in substantially identical diameter.

6. (Original) The semiconductor device according to claim 4, wherein said plurality of layers of the connecting conductor are formed in different diameters from each other in sequence of layers.

7. (Currently Amended) A semiconductor device comprising:
a semiconductor chip,
a protective insulating layer comprising a coating layer covering the surface of the semiconductor chip;
a plurality of connecting conductors connected to the surface of the semiconductor chip and penetrating the coating layer beyond the outside surface of the coating layer, wherein the connecting conductors are connected to bumps as external terminals beyond the outside surface of the coating layer, and wherein the connecting conductors do not include wiring layers and the bumps;
wherein the connecting conductor includes a plurality of layers formed of different material and at least one of the layers is formed as a stress-absorbing layer having lower hardness than other layer.

8. (Original) The semiconductor device according to claim 7, wherein said stress-absorbing layer is formed from gold and palladium.

9. (Original) The semiconductor device according to claim 7, wherein said stress-absorbing layer is formed from anisotropic conductive material.
10. (Original) The semiconductor device according to claim 7, wherein said stress-absorbing layer is formed from conductive material containing metal particles.
11. (Original) The semiconductor device according to claim 7, wherein said connecting conductor is formed by means of stacking the plurality of layers in a staggered manner.
12. (Original) The semiconductor device according to claim 11, wherein said plurality of layers of the connecting conductor is formed in substantially identical diameter.
13. (Original) The semiconductor device according to claim 11, wherein said plurality of layers of the connecting conductor are formed in different diameters from each other in sequence of layers.